

Received 6-30-06

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FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Appy. Docket No. FIS920030236US1		Application No. 10/605,906	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use several sheets if necessary)				Applicant An L. STEEGEN et al.			
				Filing Date 11/05/2003		Group 2813	
<b>U.S. PATENT DOCUMENTS</b>							
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EXAMINER <i>Stephen W. Smoot</i>				DATE CONSIDERED <i>August 1, 2006</i>			
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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EXAMINER		Stephen W. Smoot			DATE CONSIDERED			August 1, 2006
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